20th2TO"4TO/500I

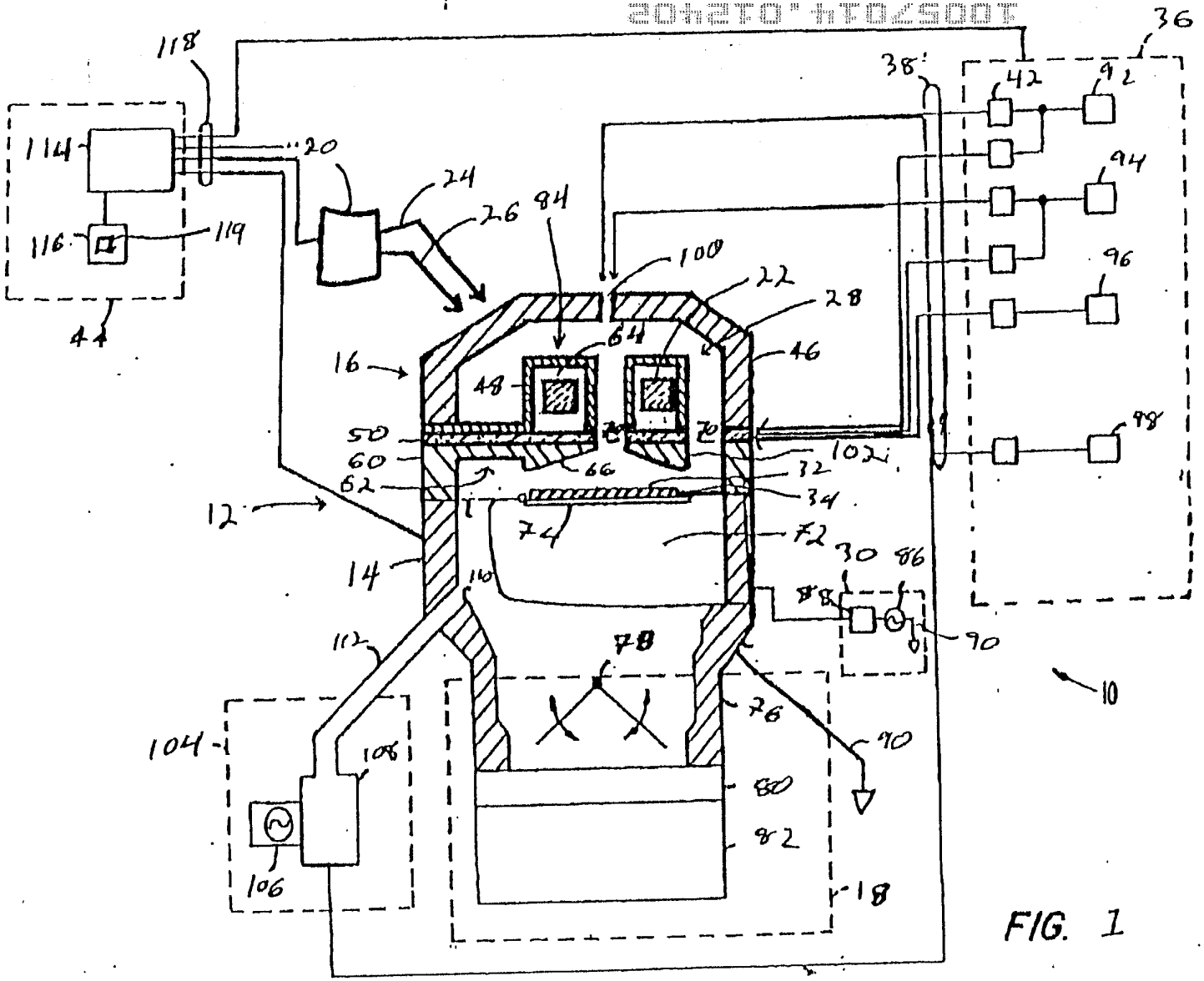


FIG. 1

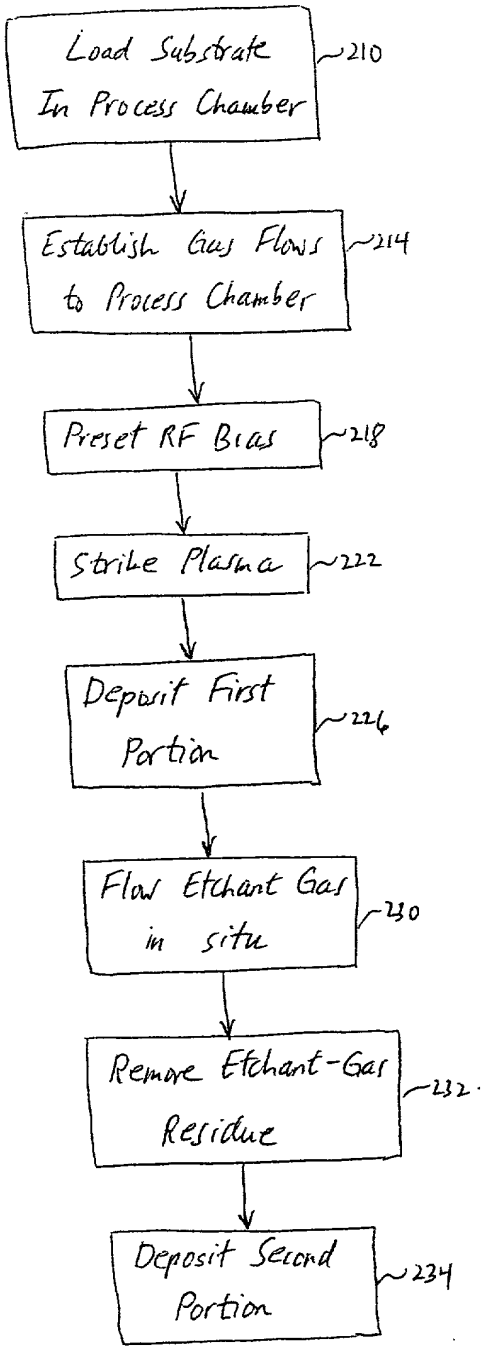

Load Substrate In Process Chamber
210
Establish Gas Flows to Process Chamber
214
Preset RF Bias
218
Strike Plasma
222
Deposit First Portion
226
Flow Etchant Gas in situ
230
Remove Etchant-Gas Residue
232
Deposit Second Portion
234

Fig. 2

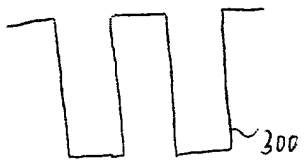


Fig. 3A

PRIOR ART

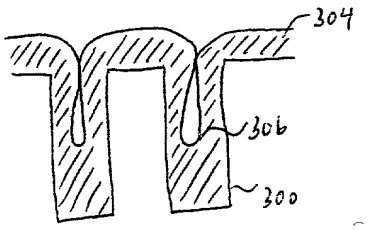


Fig. 3B

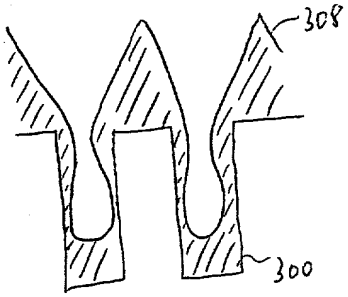


Fig. 3C

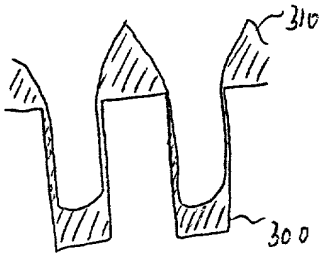
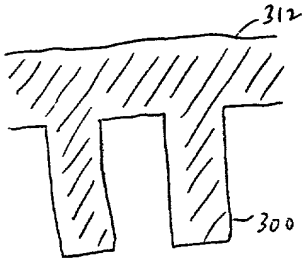


Fig. 3D



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